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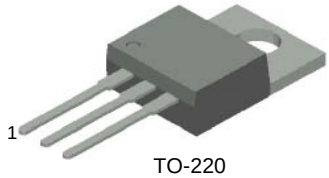
Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

November 2008

FJP1943
PNP Epitaxial Silicon Transistor

Applications

- High-Fidelity Audio Output Amplifier
- General Purpose Power Amplifier



TO-220

1.Base 2.Collector 3.Emitter

Features

- High Current Capability: I_C = -15A.
- High Power Dissipation : 80watts.
- High Frequency : 30MHz.
- High Voltage : V_{CEO}= -230V
- Wide S.O.A for reliable operation.
- Excellent Gain Linearity for low THD.
- Complement to FJP5200
- Full thermal and electrical Spice models are available.
- Same transistor is also available in:
  -- TO264 package, 2SA1943/FJL4215 : 150 watts
  -- TO3P package, 2SA1962/FJA4213 : 130 watts
  -- TO220F package, FJPF1943 : 50 watts

Absolute Maximum Ratings* T_a = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
BV_{CBO}	Collector-Base Voltage	-230	V
BV_{CEO}	Collector-Emitter Voltage	-230	V
BV_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-15	A
I_B	Base Current	-1.5	A
P_D	Total Device Dissipation(T_C=25°C) Derate above 25°C	80 0.64	W W/°C
T_J, T_{STG}	Junction and Storage Temperature	- 50 ~ +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.25	°C/W

* Device mounted on minimum pad size

h_{FE} Classification

Classification	R	O
h_{FE1}	55 ~ 110	80 ~ 160

Electrical Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C=-5mA, I_E=0	-230			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C=-10mA, R_{BE}=∞	-230			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E=-5mA, I_C=0	-5			V
I_{CBO}	Collector Cut-off Current	V_{CB}=-230V, I_E=0			-5.0	μA
I_{EBO}	Emitter Cut-off Current	V_{EB}=-5V, I_C=0			-5.0	μA
h_{FE1}	DC Current Gain	V_{CE}=-5V, I_C=-1A	55		160	
h_{FE2}	DC Current Gain	V_{CE}=-5V, I_C=-7A	35	60		
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C=-8A, I_B=-0.8A		-0.4	-3.0	V
V_{BE}(on)	Base-Emitter On Voltage	V_{CE}=-5V, I_C=-7A		-1.0	-1.5	V
f_T	Current Gain Bandwidth Product	V_{CE}=-5V, I_C=-1A		30		MHz
C_{ob}	Output Capacitance	V_{CB}=-10V, f=1MHz		360		pF

* Pulse Test: Pulse Widt=20μs, Duty Cycle≤2%

Ordering Information

Part Number	Marking	Package	Packing Method	Remarks
FJP1943RTU	J1943R	TO-220	TUBE	hFE1 R grade
FJP1943OTU	J1943O	TO-220	TUBE	hFE1 O grade

Typical Characteristics

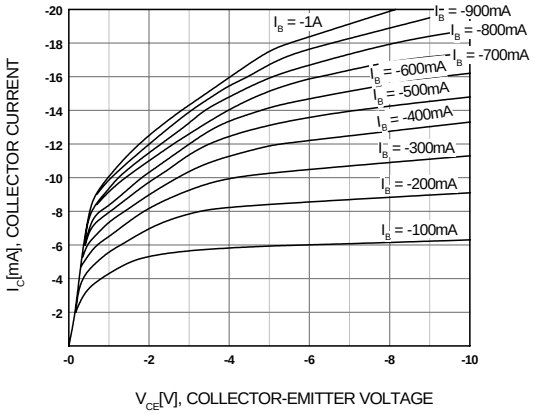


Figure 1. Static Characteristic

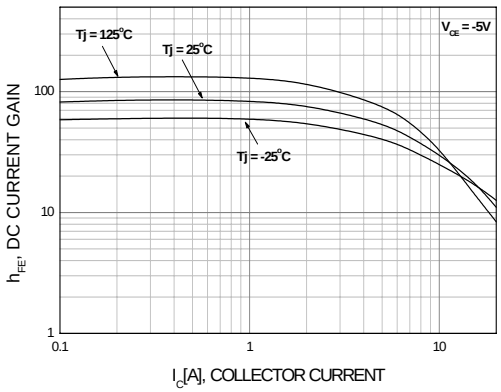


Figure 2. DC current Gain (R Grade)

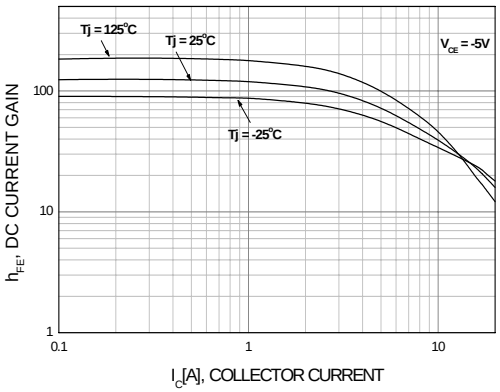


Figure 3. DC current Gain (O Grade)

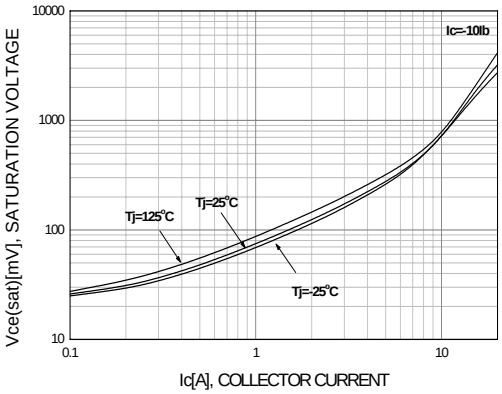


Figure 4. Collector-Emitter Saturation Voltage

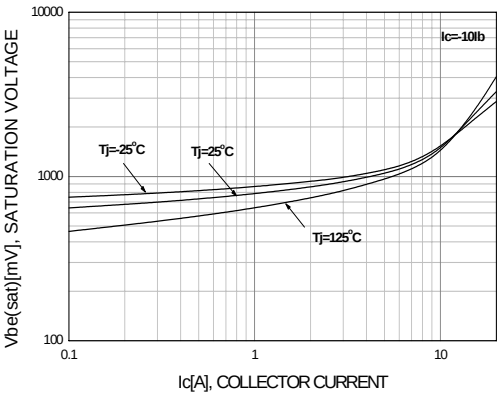


Figure 5. Base-Emitter Saturation Voltage

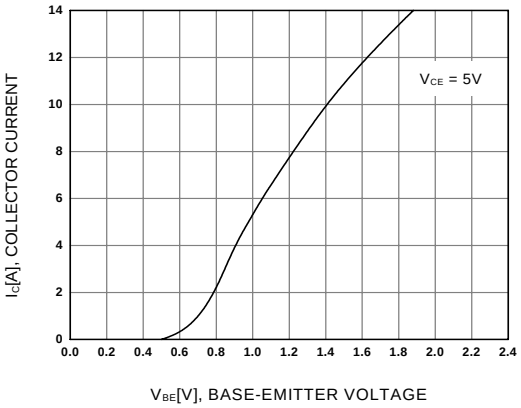


Figure 6. Base-Emitter On Voltage

Typical Characteristics

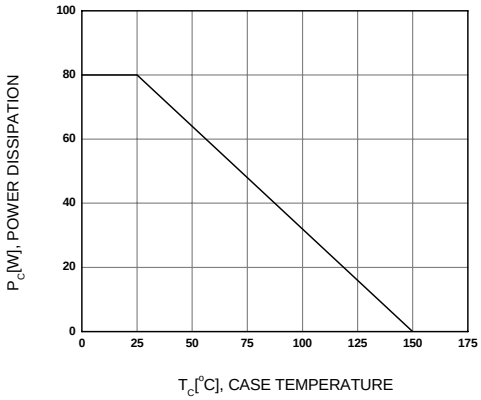


Figure 7. Power Derating

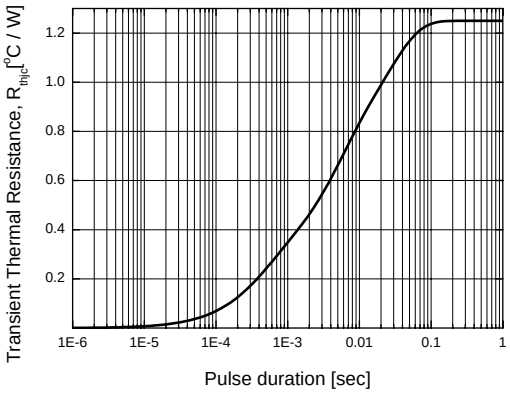
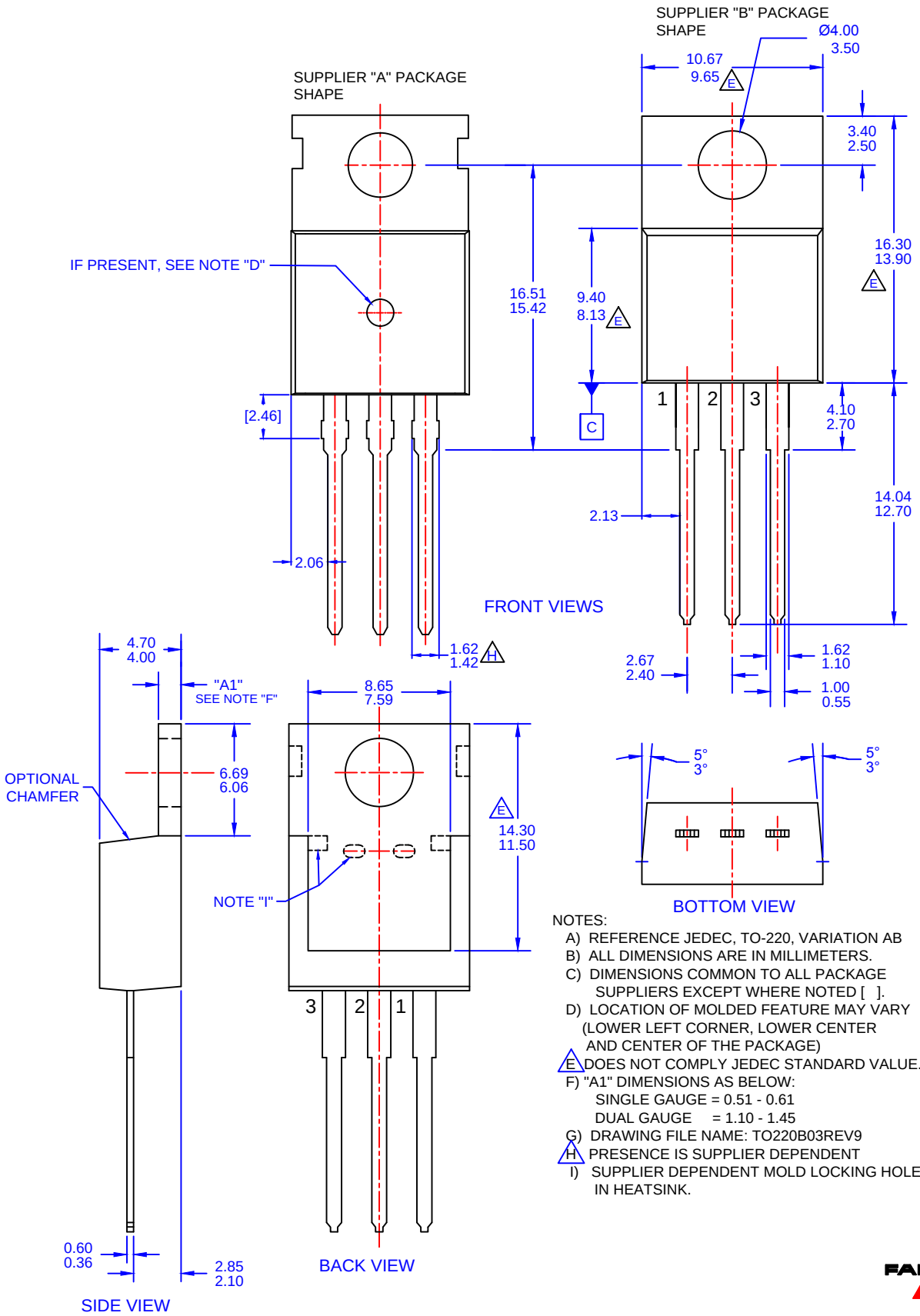


Figure 8. Thermal Resistance



NOTES:

A) REFERENCE JEDEC, TO-220, VARIATION AB
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS COMMON TO ALL PACKAGE SUPPLIERS EXCEPT WHERE NOTED [ ].
D) LOCATION OF MOLDED FEATURE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE)
E DOES NOT COMPLY JEDEC STANDARD VALUE.
F) "A1" DIMENSIONS AS BELOW:
SINGLE GAUGE = 0.51 - 0.61
DUAL GAUGE = 1.10 - 1.45
G) DRAWING FILE NAME: TO220B03REV9
H PRESENCE IS SUPPLIER DEPENDENT
I) SUPPLIER DEPENDENT MOLD LOCKING HOLES IN HEATSINK.

FAIRCHILD

PUBLICATION ORDERING INFORMATION

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